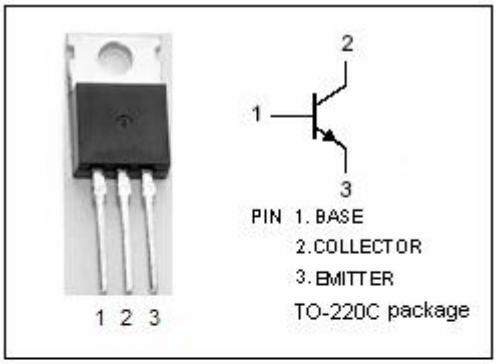
isc Silicon NPN Power Transistor — BUL6825

DESCRIPTION

- Collector–Emitter Sustaining Voltage
  : $V_{CEO(SUS)}$ = 400V(Min.)
- Low Collector Saturation Voltage
  : $V_{CE(sat)}$ = 0.5V(Max) @ I_C= 1A
- High Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

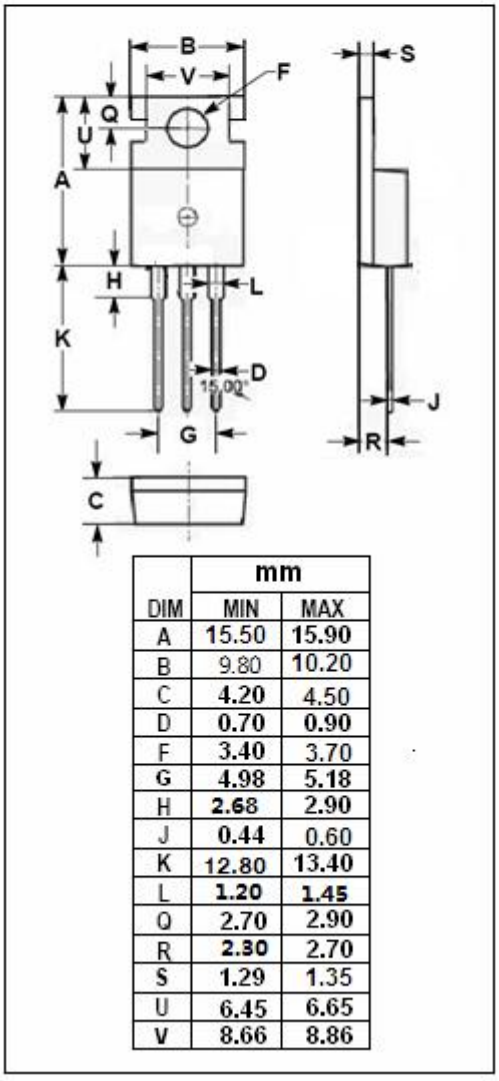
- Designed for use in relay drivers ,inverters ,switching regulators and deflection circuits applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-peak	8	A
I_B	Base Current-Continuous	2	A
I_{BM}	Base Current-peak	4	A
P_C	Collector Power Dissipation T_C=25℃	75	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.67	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C =25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 10mA; Ib=0	400			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 1A; I_B= 0.2A			0.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 0.5A			0.6	V
$V_{CE(sat)-3}$	Collector-Emitter Saturation Voltage	I_C= 4A; I_B= 1A			1.0	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 1A; I_B= 0.2A			1.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= 2A; I_B= 0.5A			1.6	V
I_{CBO}	Collector Cutoff Current	V_{CB}=700V ;I_E=0 T_C=100℃			1.0 5.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 9V; I_C= 0			1.0	mA
h_{FE-1}	DC Current Gain	I_C= 1A; V_{CE}= 5V	10		60	
h_{FE-2}	DC Current Gain	I_C= 2A; V_{CE}= 5V	8		40	
C_{OB}	Output Capacitance	V_{CB}= 10V; f_{test}= 1MHz		65		pF
f_T	Current-Gain—Bandwidth Product	I_C=0.5A;V_{CE}=5V	4			MHz
Switching Times, Inductive Load						
t_d	Delay time	V_{CC}= 125V;I_C= 2A;I_{B1}=I_{B2}= 0.4A			0.1	μs
t_r	Rise time				0.7	μs
t_s	Storage Time				4.0	μs
t_f	Fall Time				0.9	μs

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